



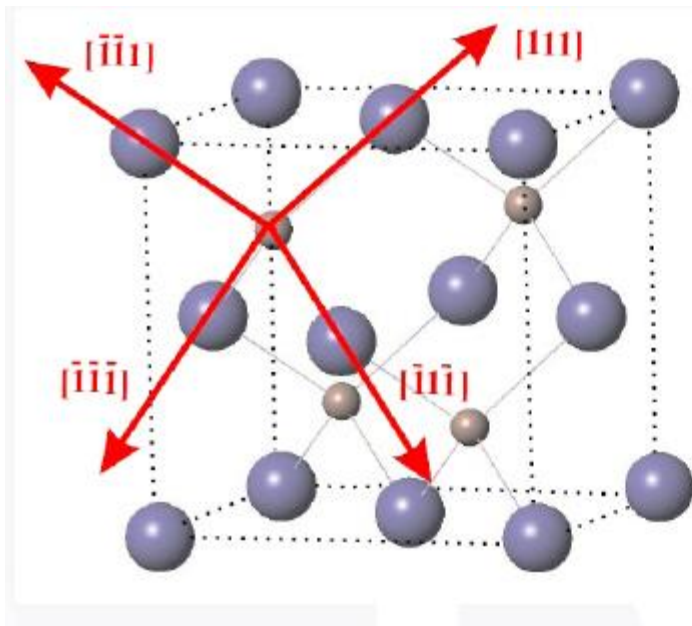
Effects of Crystal Orientation on the Optical Properties of GaN based Devices

Outline

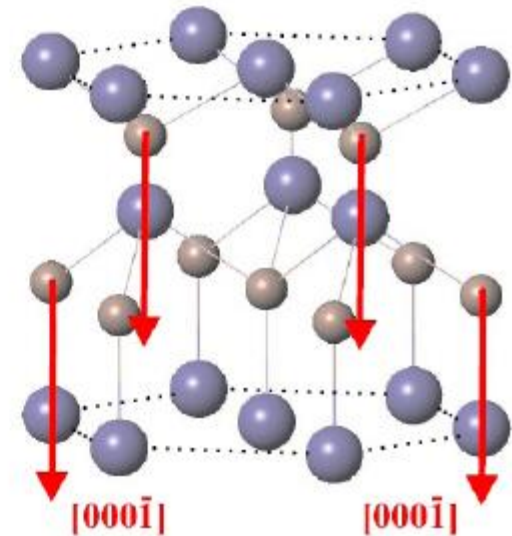
- Crystal orientation and polarization
- k.p method for QW of arbitrary orientation
- Results for InGaN/GaN QW
- LD performance

Spontaneous Polarization

Cubic
zero net polarization



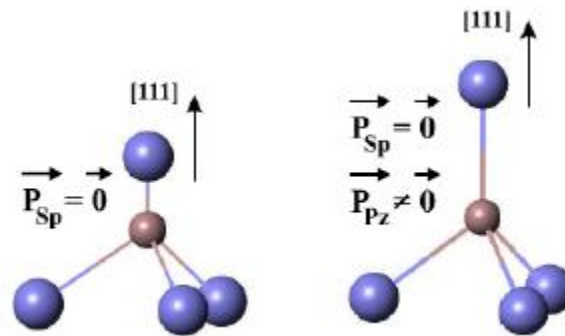
Hexagonal
Non-zero net
polarization



N. G. Thillosen (PhD thesis: Spin-Bahn-Wechselwirkung in niedrigdimensionalen $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ -Elektronengasen)

Piezoelectric polarization

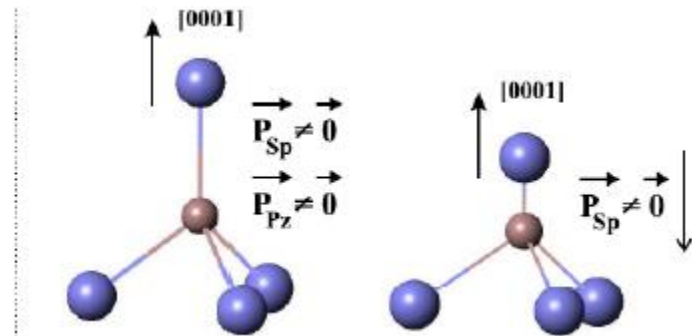
Cubic



No strain

Bi-axial strain

Hexagonal

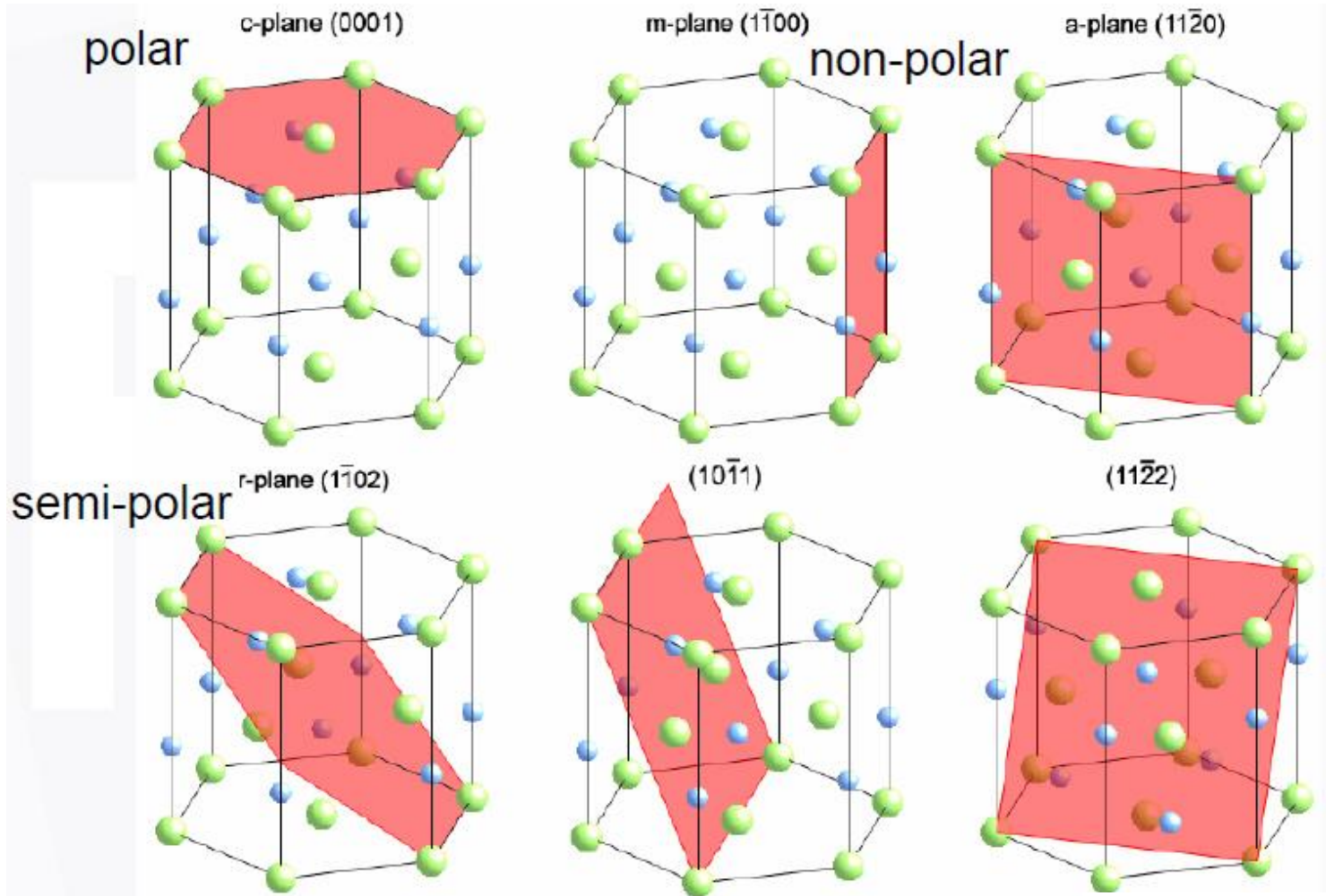


No strain

Bi-axial strain

N. G. Thillosen (PhD thesis: Spin-Bahn-Wechselwirkung in niedrigdimensionalen $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ -Elektronengasen)

Alternative growth orientations



Band structure

- Conduction band is treated by parabolic model

$$\Psi_n^{c\eta}(z, \vec{k}_t) = \frac{1}{\sqrt{V}} e^{i\vec{k}_t \cdot \vec{r}_t} \phi_n(z) |S\eta\rangle$$

S is spherical wavefunction, η is spin, $\phi_n(z)$ is the envelope function of n th subband

Valence band

- Valence band is treated by 6x6 k.p method, including top three valence bands

$$H(\vec{k}, \varepsilon) = H(\vec{k}) + D(\varepsilon) \leftarrow \text{strain}$$

$$H(\vec{k}, \varepsilon) |\Psi\rangle = E(\vec{k}) |\Psi\rangle$$

For quantum well

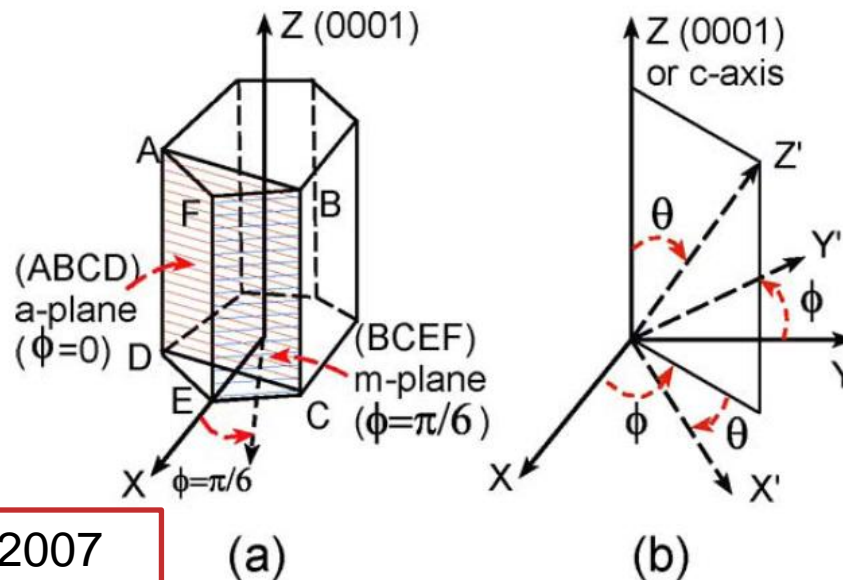
$$\Psi_m^v(z, \vec{k}_t) = \frac{1}{\sqrt{V}} e^{i\vec{k}_t \cdot \vec{r}_t} \sum_{i=1}^6 g_m^i(z, \vec{k}_t) U^i$$

g_m is the envelope function of the m th subband
 U^i are basis functions

Rotation

Hamiltonian for arbitrary rotation $H(k')$
can be obtained by rotation matrix

$$U = \begin{pmatrix} \cos \theta \cos \phi & \cos \theta \sin \phi & -\sin \theta \\ -\sin \phi & \cos \phi & 0 \\ \sin \theta \cos \phi & \sin \theta \sin \phi & \cos \theta \end{pmatrix}$$



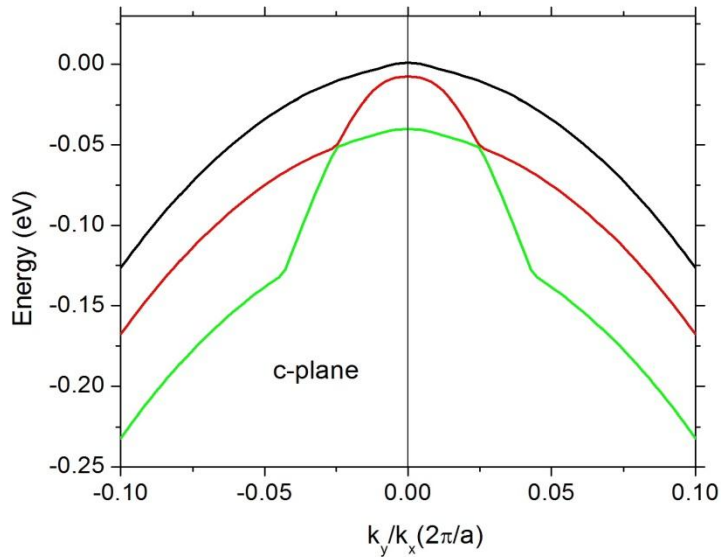
Strain tensor for arbitrary crystal orientation

- Strain coefficients for arbitrary crystal orientation are calculated by minimizing the elastic energy under the conditions for pseudo-morphic growth.

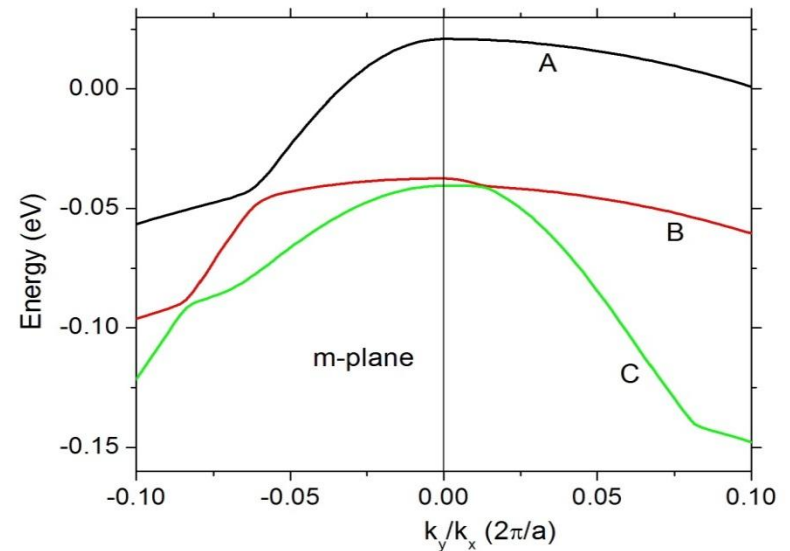
$$W = \frac{1}{2} \sum_{i=1}^6 \sum_{j=1}^6 \int C_{ij} \varepsilon_i \varepsilon_j dV$$

PRB, v59, 4725, 1999

Anisotropic band structure



c-plane: isotropic



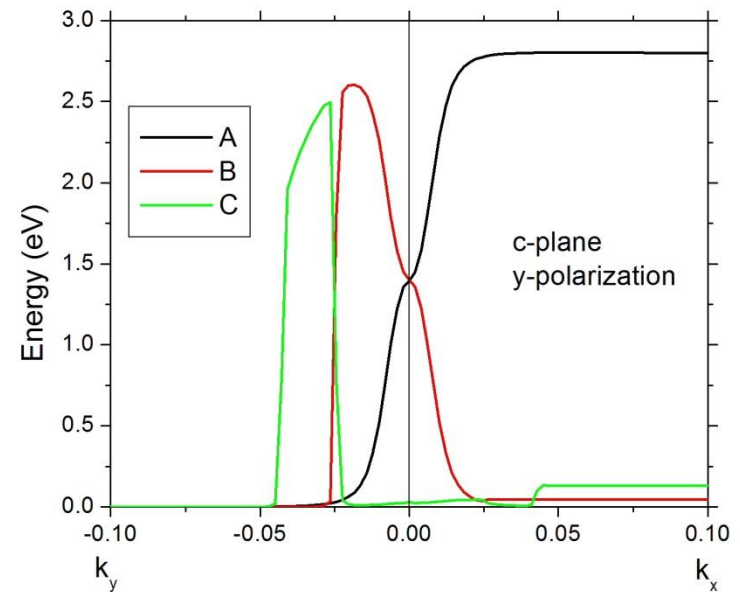
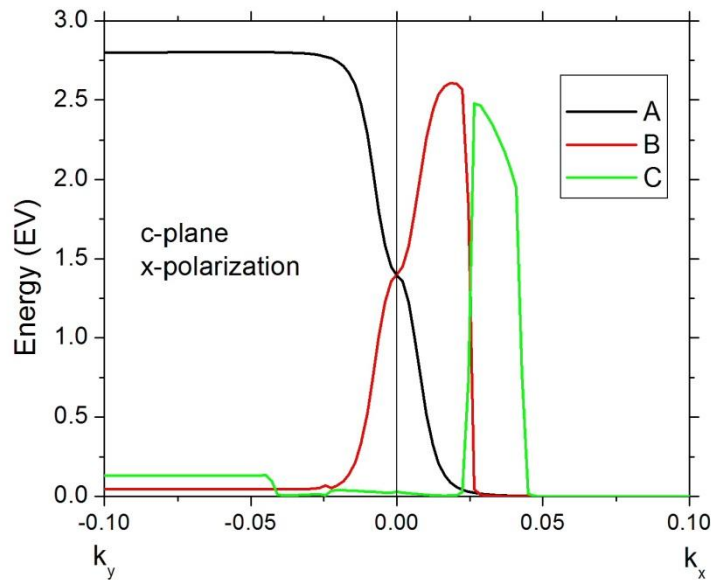
m-plane: anisotropic
band structure.
Smaller effective
mass in y-direction

Optical momentum matrix

Optical momentum matrix elements for transition between conduction band n and valence band m are defined as

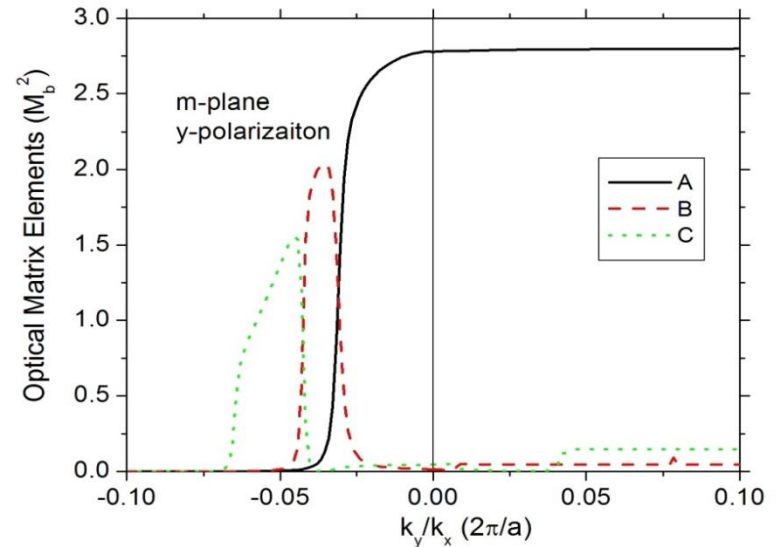
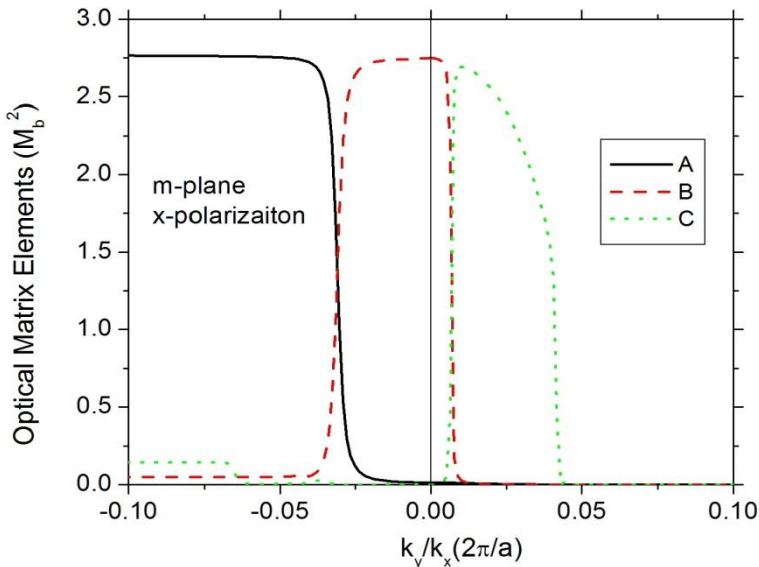
$$\begin{aligned} |M_{nm}^{\eta}|^2 &= |\hat{e} \cdot M^{\eta}|^2 \\ &= |\langle \Psi_n^{c\eta} | \hat{e} \cdot p | \Psi_m^v \rangle|^2 \end{aligned}$$

Optical matrix elements: c-plane



A,B,C are for transitions from conduction band to top three valence bands. Integrating over (k_x-k_y) plane, optical matrix elements are NOT dependent on E-field polarization on x-y plane.

Optical matrix elements: m-plane



A,B,C are for transitions from conduction band to top three valence bands. Optical matrix elements are dependent on polarization.

Optical gain

- Optical gain is calculated by

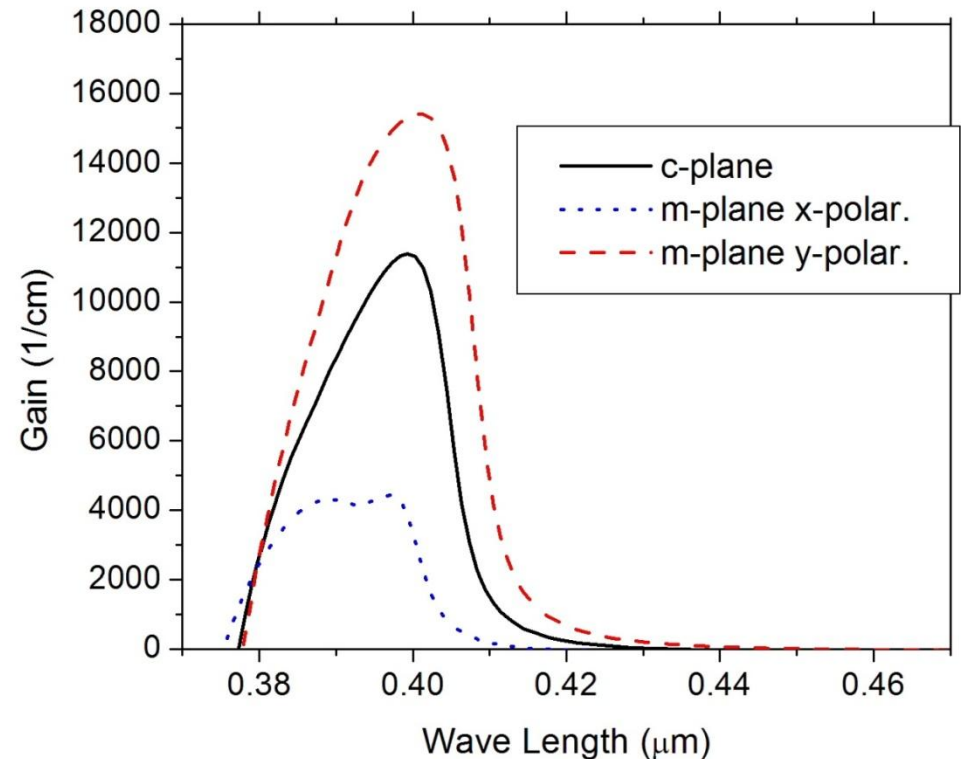
$$g(\omega) = \frac{q^2}{n_r c \epsilon_0 m_0^2 \omega d_\omega} \sum_{n,m,\eta} \int d\vec{k}_t |M_{nm}^\eta|^2 [f_n^c - f_m^v] L(\omega)$$

$L(\omega)$ is broadening function. Note 2D integration is necessary except for c-plane QWs, where the band structure is isotropic. Similar 2D integration for spontaneous rates as well.

Optical gain for different orientations

30nm-In₁₅Ga₈₅N/GaN
Quantum well at
carrier density of
6.67e25/m³

No polarization
charge in all cases



Effects of crystal orientation: from c-plane to m-plane

- No polarization charge
- Optical gain: polarization dependent, enhanced in y-polarization
- Transport: effective mass is reduced

How do these affect the laser performance?

Laser performance: finite-element simulation

Edge-emitting laser active region:
30-nm $\text{In}_{15}\text{Ga}_{85}\text{N}/\text{GaN}$ QW (x3)

No polarization charges in all cases

